

W

E502650

Features

- Low V_{CE(sat)} With SPT+ Technology
- V_{CE(sat)} With Positive Temperature Coefficient
- · Including Fast & Soft Recovery Anti-parallel FWD
- High Short Circuit Capability(10us)
- Low Inductance Module Structure
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Applications

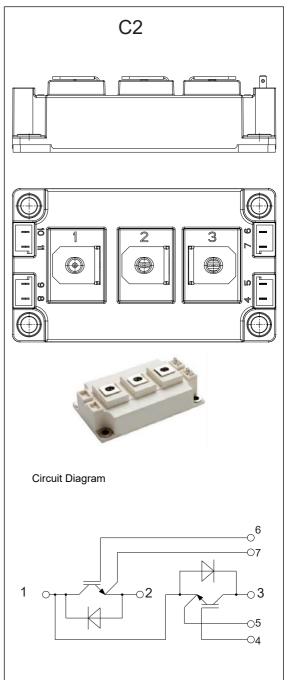
- · Inverter for Motor Drive
- AC and DC Servo Driver Amplifier
- UPS(Uninterruptible Power Supplies)
- Soft Switching Welding Machine

Maximum Ratings

- Maximum Junction Temperature: 175°C
- Operating Junction Temperature Range: -40°C to +150°C
- Storage Temperature Range: -40°C to +125°C
- IGBT Thermal Resistance: 0.065 K/W Junction to Case
- Diode Thermal Resistance: 0.13 K/W Junction to Case
- Type Conductive Grease Applied Thermal Resistance: 0.033K/W Junction to Case-To-Sink

Parameter	Symbol	Rating	Unit	
	V _{CES}	CES 1200		
Continuous Collector Current @	I _C	450	Α	
Peak Collector Current @Tp=1ms		I _{CRM}	900	Α
Gate-Emitter Voltage@T _{vj} =25°C		V_{GE}	±20	V
Isolation Voltage @f=50Hz, t=1min		$V_{\rm iso}$	2500(Min)	V
Weight of Module		G	315	g
Module Electrodes Torque:M5		M _t	3~5	N*m
Module-to-Sink Torque :M6		Ms	3~5	N*m
Total Tower Dissipation	T _C =25°C T _{vjmax} =175°C	P _{tot}	2307	W

IGBT Modules 1200V 450A





Electrical Characteristics of IGBT @ 25°C (Unless Otherwise Specified)

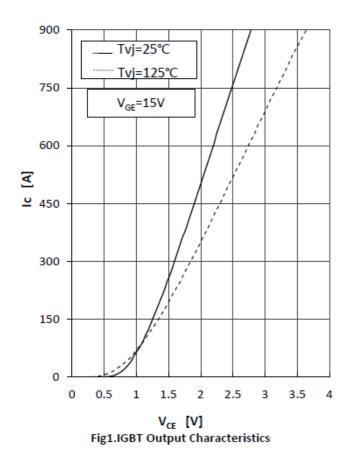
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} =V _{GE,} I _C =12mA,T _{vj} =25°C	5.2	5.8	6.4	V	
Collector-Emiter Cut-off Current	I _{CES}	V _{CE} =1200V, V _{GE} =0V,T _{vj} =25°C			1.0	- mA	
		V _{CE} =1200V, V _{GE} =0V,T _{vj} =125°C			5		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _C =450A,T _{vj} =25°C		1.90	2.35	\/	
		V _{GE} =15V, I _C =450A,T _{vj} =125°C		2.30		V	
Gate Charge	Q_{G}			3.62		uC	
Input Capacitance	C _{ies}	V _{CE} =25V,V _{GE} =0V,f=1MHz,		25			
Reverse Transfer Capacitance	C _{res}	T _{vj} =25°C		1.1		nF	
Internal Gate Resistance	Rgint			0.7		Ω	
Gate Emitter Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =20V,T _{vj} =25°C			400	nA	
Turn-On Delay Time	t _{d(on)}			161			
Rise Time	t _r	V 000V		52		ns	
Turn-Off Delay Time	$t_{d(off)}$	V_{CE} =600V, I_{C} =450A, V_{GE} = \pm 15V, R_{G} =1.8 Ω , Tvj=25°C		502			
Fall Time	T _f			96			
Energy Dissipation During Turn-on Time	E _{on}			23.2		1	
Energy Dissipation During Turn-off Time	E _{off}			28.5		mJ	
Turn-On Delay Time	t _{d(on)}			192			
Rise Time	t _r	V_{CE} =600V, I_{C} =450A, V_{GE} = \pm 15V, R_{G} =1.8 Ω , Tvj=125°C		63			
Turn-Off Delay Time	t _{d(off)}			536		ns	
Fall Time	T _f			135			
Energy Dissipation During Turn-on Time	E _{on}			31.5		m l	
Energy Dissipation During Turn-off Time	E _{off}			44.3		mJ	
SC data	I _{SC}	$T_P \le 10$ us, $V_{GE} = 15$ V, $T_{Vj} = 150$ °C, $V_{CC} = 600, V_{CEM} \le 1200$ V		1800		А	

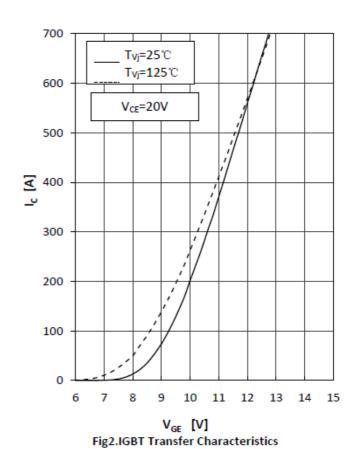


Electrical Characteristics of DIODE @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Diode DC Forward Current	I _F	T _C =100°C		450		Α
Diode Peak Forward Current	I _{FRM}	I _{FRM} =2I _F		900		Α
Forward Voltage	V_{F}	I _F =450A, T _{vj} =25°C		2.1		V
	V F	I _F =450A, T _{vj} =125°C		2.15		
Recovered Charge	Q_{rr}	V_R =600V, I_F =450A, - di_F / dt =6500A/ us , T_{vj} =25°C		45		uC
Peak Revere Recovery Current	I _{rr}			383		Α
Reverse Recovery Energy	E _{rec}			21.2		mJ
Recovered Charge	Q _{rr}	V _R =600V, I _F =450A, -di _F /dt=9000A/us, T _{vj} =125°C		86		uC
Peak Revere Recovery Current	I _{rr}			453		Α
Reverse Recovery Energy	E _{rec}			37.2		mJ

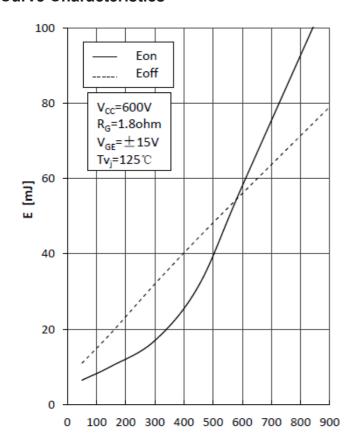
Curve Characteristics



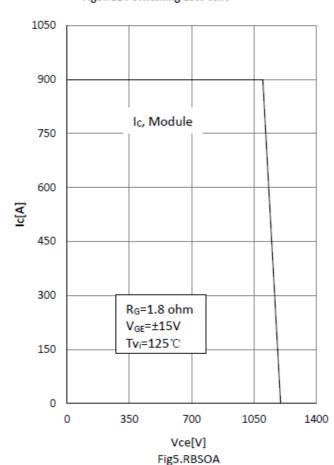


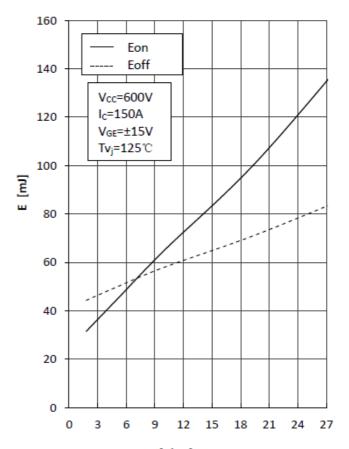


Curve Characteristics

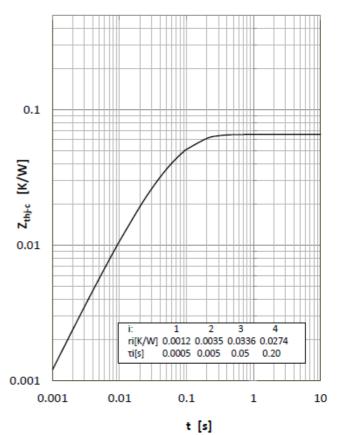


I_C [A] Fig3.IGBT Switching Loss vs.Ic



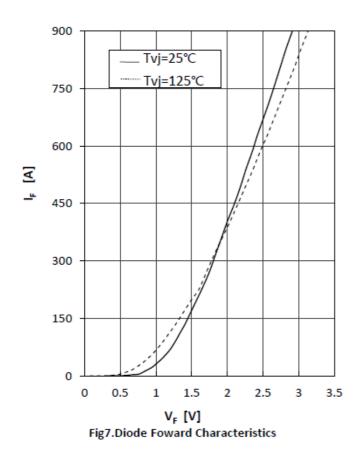


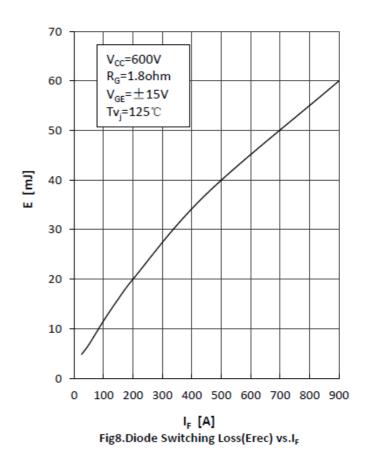
Rg [ohm] Fig4.IGBT Switching Loss vs.Rg

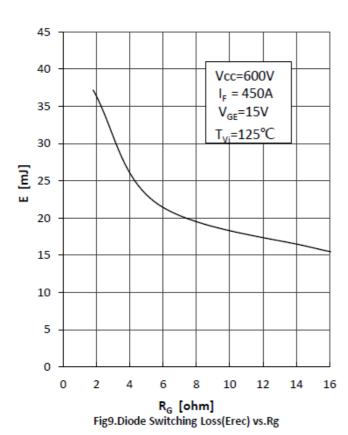


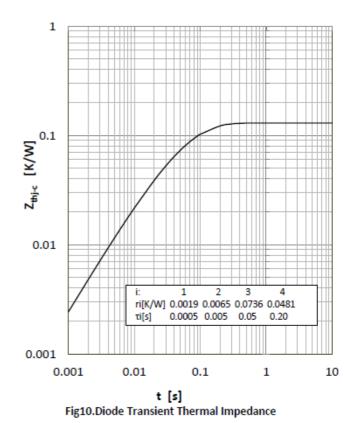


Curve Characteristics





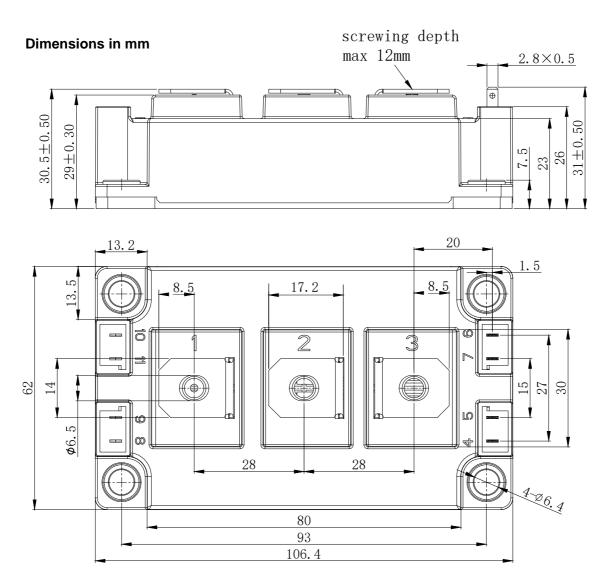






Package Dimensions

C2





Ordering Information

Device	Packing	
Part Number-BP	Bulk: 6pcs/Box ; 30pcs/Ctn	

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